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Microsemi.

# Power Matters<sup>™</sup>

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### 2N4915 (#23235)

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## Overview Diagrams

Electrical Rating	Symbol	Min	Тур	Max	Unit
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>			0.75	V
DC Current Gain	HFE	25.00		100.00	

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V <sub>BR(CBO)</sub>			80.00	V
Collector Current (dc)	I <sub>C</sub>			5.00	А
Collector-Emitter Voltage (Base Open)	$V_{CEO}$			80.00	V
Emitter-Base Voltage (Collector Open)	V <sub>EBO</sub>			5.00	V
Power Dissipation, Total	P <sub>T</sub>			88.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT( BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices Transistors BJT( BiPolar Junction Transistor) NPN Transistor

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